

April 2011

# FMBS2383 NPN Epitaxial Silicon Transistor

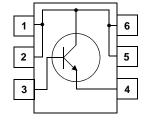
#### **Features**

• Power Amplifier

 $\bullet \ \ Collector\text{-Emitter Voltage}: V_{CEO}\text{=}160V \\$ 

• Current Gain Bandwidth Product : f<sub>T</sub>=120MHz





## **Absolute Maximum Ratings** $T_a = 25$ °C unless otherwise noted

| Symbol            | Parameter                               | Value       | Units |
|-------------------|---|-------------|-------|
| V <sub>CBO</sub>  | Collector-Base Voltage                  | 160         | V     |
| V <sub>CEO</sub>  | Collector-Emitter Voltage               | 160         | V     |
| V <sub>EBO</sub>  | Emitter-Base Voltage                    | 5           | V     |
| I <sub>C</sub>    | Collector Current                       | 800         | mA    |
| I <sub>B</sub>    | Base Current                            | 160         | mA    |
| $P_{D}$           | Power Dissipation                       | 630         | mW    |
| $R_{\theta JA}^*$ | Thermal Resistance, Junction to Ambient | 200         | °C/W  |
| T <sub>J</sub>    | Junction Temperature                    | 150         | °C    |
| T <sub>STG</sub>  | Storage Temperature                     | -55 to +150 | °C    |

<sup>\*</sup> note1) : Minimum land pattern size

### **Electrical Characteristics** $T_a = 25^{\circ}C$ unless otherwise noted

| Symbol                | Parameter                            | Test Condition                            | Min. | Тур. | Max. | Units |
|-----------------------|--------------------------------------|---|------|------|------|-------|
| BV <sub>CBO</sub>     | Collector-Base Breakdown Voltage     | $I_C = 10\mu A, I_B = 0$                  | 160  |      |      | V     |
| BV <sub>CEO</sub>     | Collector-Emitter Breakdown Voltage  | $I_C = 10 \text{mA}, I_B = 0$             | 160  |      |      | V     |
| BV <sub>EBO</sub>     | Emitter-Base Breakdown Voltage       | $I_E = 1mA$ , $I_C = 0$                   | 5    |      |      | V     |
| I <sub>CBO</sub>      | Collector Cut-off Current            | $V_{CB} = 120V, I_{E} = 0$                |      |      | 100  | nA    |
| I <sub>EBO</sub>      | Emitter Cut-off Current              | $V_{BE} = 5V, I_{C} = 0$                  |      |      | 100  | nA    |
| h <sub>FE</sub>       | DC Current Gain                      | $V_{CE} = 5V, I_{C} = 100mA$              | 80   |      | 160  |       |
| V <sub>CE</sub> (sat) | Collector-Emitter Saturation Voltage | $I_C = 500 \text{mA}, I_B = 50 \text{mA}$ |      |      | 1.0  | V     |
| V <sub>BE</sub> (on)  | Base-Emitter On Voltage              | $V_{CE} = 5V, I_{C} = 500 \text{mA}$      |      |      | 1.0  | V     |
| f <sub>T</sub>        | Current Gain Bandwidth Product       | $V_{CE} = 5V, I_{C} = 100mA$              |      | 120  |      | MHz   |
| C <sub>ob</sub>       | Output Capacitance                   | $V_{CB} = 10V, I_E = 0, f = 1MHz$         |      |      | 30   | pF    |

## **Typical Performance Characteristics**

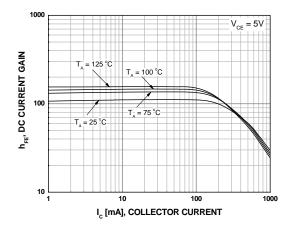


Figure 1. DC Current Gain

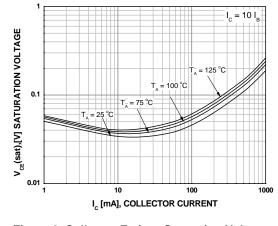


Figure 2. Collector-Emitter Saturation Voltage

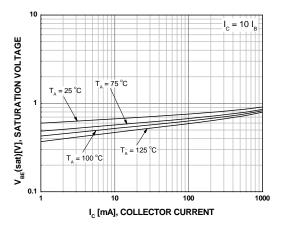


Figure 3. Base-Emitter Saturation Voltage

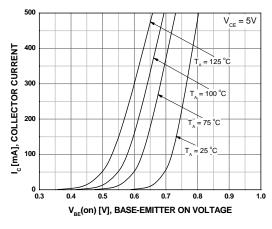


Figure 4. Base-Emitter On Voltage

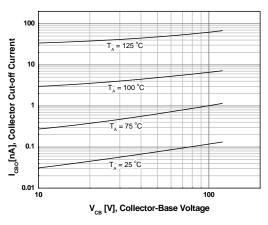


Figure 5. Collector-Base Cutoff Current

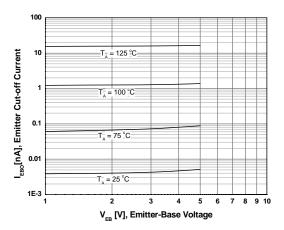


Figure 6. Emitter-Base Cutoff Current

## **Typical Performance Characteristics** (Continued)

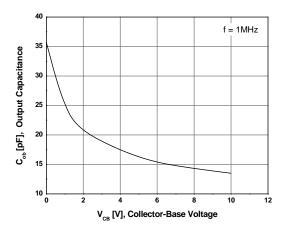


Figure 7. Output Capacitance

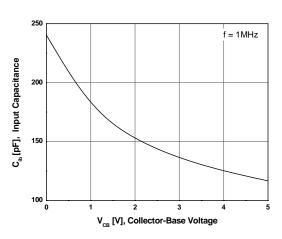


Figure 8. Input Capacitance

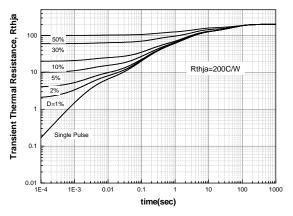
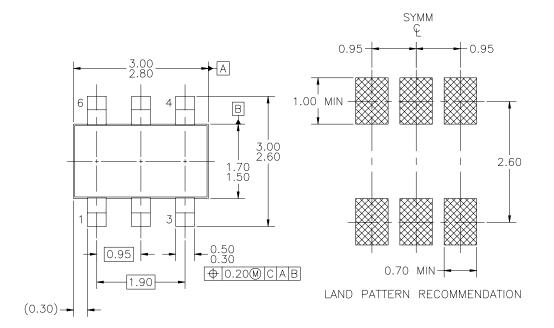
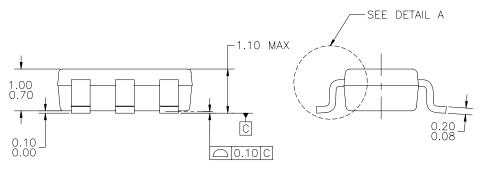


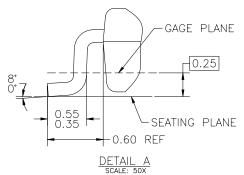
Figure 9. Transient Thermal Resistance

## **Physical Dimensions**

# SuperSOT™-6







NOTES: UNLESS OTHERWISE SPECIFIED

- THIS PACKAGE CONFORMS TO JEDEC MO-193. VAR. AA, ISSUE C, DATED JANUARY 2000. ALL DIMENSIONS ARE IN MILLIMETERS.

Dimensions in Millimeters





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